

Substitute Form PTO-1449 (Modified) Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12967-002001	Application No. 09/824,965
	Applicant Tomohiro Kawase et al		
	Filing Date April 3, 2001	Group Art Unit 1765	

U.S. Patent Documents

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
<i>AK</i>	AA	5,342,475	8/1994	Yoshida et al.	117/83		
	AB	5,454,346	10/1995	Uchida et al.	117/13		
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

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Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
<i>AK</i>	AL	0 417 843 A2	Mar. 20, 1991	EPO				
	AM	0529963B1	Aug. 21, 1992	EPO				
	AN	04-104989	Apr. 7, 1992	Japan			Abs	
	AO	06-128096	May 10, 1994	Japan			Abs	
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
<i>AK</i>	AQ	Parsey, "Relative virtues of different growth techniques" in Semi-Insulating III-V Materials. 1988.
	AR	Doering et al, "Carbon incorporation into LEC GaAs" in Semi-Insulating III-V Materials. 1990.
	AS	Müller et al, "Current issues in bulk growth of s.i. III-V materials" in Semi-Insulating III-V Materials. 1992.
	AT	Doering et al., "Carbon Incorporation Into LEC GaAs. Int. Conf. Semi-conducting and Semi-Insulating GaAs." Malmö, Sweden (1984)
	AU	Desnica et al., "Distribution coefficient of carbon in gallium arsenide." Inst. Phys. Conf. Ser. No. 83, ch. 2, pp. 33-38 (1986)

Examiner Signature

Date Considered

3/4/02

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<i>[Handwritten Initials]</i>	AV	Desnica et al., "Distribution coefficient of carbon in melt-grown GaAs," J. Appl. Phys. 62(9) (1 Nov. 1987)
<i>[Handwritten Initials]</i>	AW	Kawase et al., "Low-dislocation-density and Low residual-strain Semi-insulating GaAs Grown by VB Method," 9 th Conf. on Semiconducting & Insulating Mat'ls-Abstracts, title, contents and p. 47 (April 29-May 3, 1996)
<i>[Handwritten Initials]</i>	AX	Kawase et al., "Low-dislocation-density and Low-residual-strain Semi-insulating GaAs Grown by Vertical Boat Method," 9 th Conf. on Semiconducting & Insulating Mat'ls-Proceedings, title, pp. ii-iii, vii-viii, xv, 275-278 (1996)

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